

Supporting Information

Sculptured Thin Film Vanadium dioxide Thermo-chromic Coatings Grown by Oblique Angle Deposition: Investigation of Transmittance Response and Modulation Enhancement by Experiment and Theoretical Modeling

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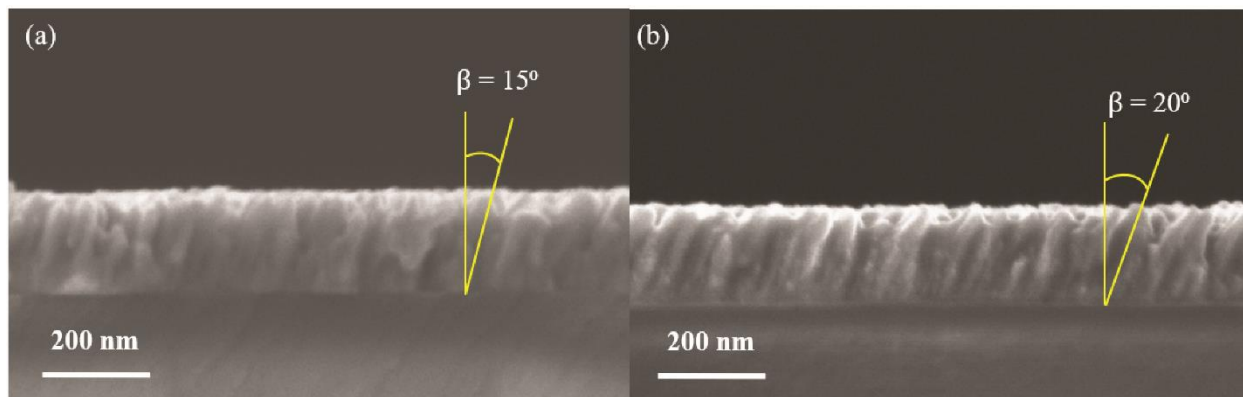


Fig. S1 SEM cross-section images of the as-prepared STF vanadium at the deposition angles (a) $\alpha = 70^\circ$ and (b) $\alpha = 80^\circ$.

Table S1. Summary of the AFM average roughness of as-prepared STF vanadium and STF VO₂ annealed at different temperatures and times

Sample code	Annealing	Annealing temperature (°C)	Annealing time (min)	Average roughness (nm)
T1	No (as-prepared sample)	-	-	2.5
T2	Yes	400	2	5.8
T3	Yes	450	2	9.5
T4	Yes	500	2	10.3
T5	Yes	450	4	8.8
T6	Yes	450	6	9.8
T7	Yes	450	8	10.0
T8	Yes	450	10	9.8

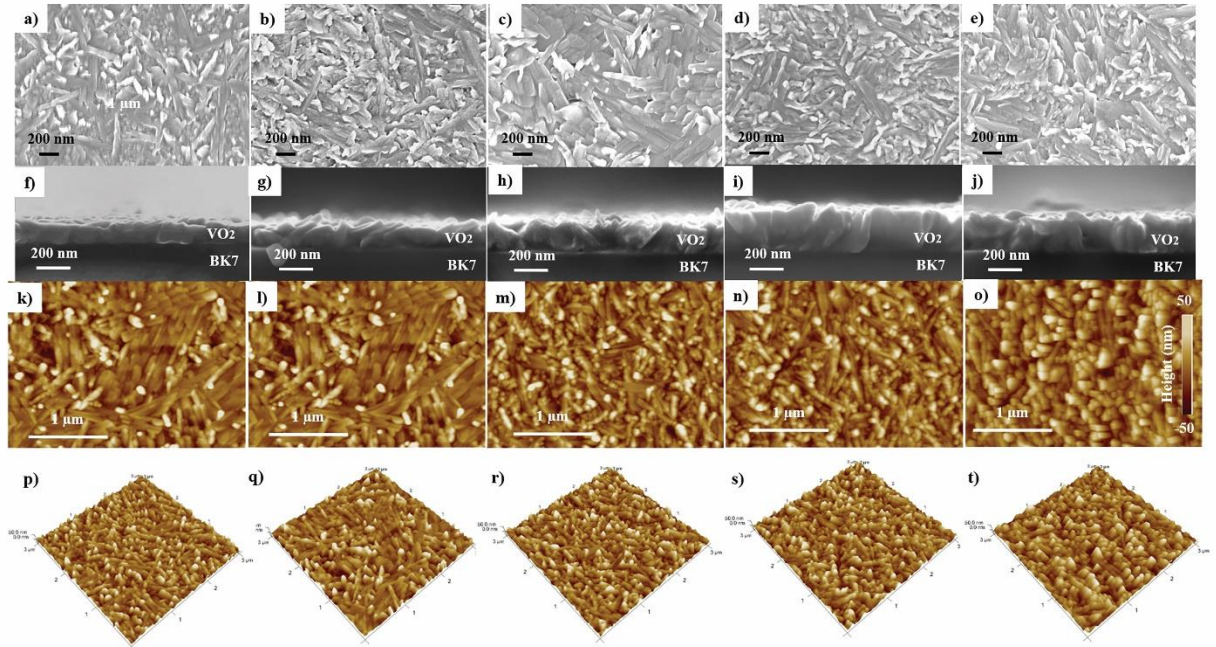


Fig. S2 SEM top-view images of the samples (a) T3 (b) T5 (c) T6 (d) T7 and (e) T8. SEM cross-section images of the samples (f) T3 (g) T5 (h) T6 (i) T7 and (j) T8. AFM 2D pictures of the samples (k) T3 (l) T5 (m) T6 (n) T7 and (o) T8. AFM 3D pictures of the samples (p) T3 (q) T5 (r) T6 (s) T7 and (t) T8. T3, T5, T6, T7, and T8 are the heat-treated samples having different annealing times maintaining a constant annealing temperature. The oxidation annealing times of the samples T3, T5, T6, T7, and T8 are 2, 4, 6, 8, and 10 min respectively, with a constant annealing temperature of 450 °C in the ambient air.

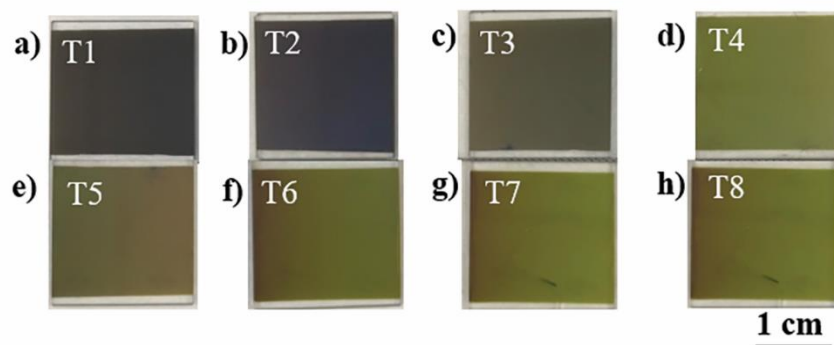


Fig. S3 Photograph of the samples (a) T1 (b) T2 (c) T3 (d) T4 (e) T5 (f) T6 (g) T7 and (h) T8. The sample T1 corresponds to as-prepared STF vanadium, whereas the samples T2 to T8 are the samples subjected to different heat-treatments having different annealing temperatures and times. The oxidation annealing temperatures of the samples T2, T3, and T4 are 400, 450, and 500 °C respectively, with a constant annealing time of 2 min in the ambient air. The oxidation annealing times of the samples T5, T6, T7 and T8 are 4, 6, 8 and 10 min respectively, with a constant annealing temperature of 450 °C in the ambient air. It is known that VO_2 is sensitive to air and prone to degradation when exposed to ambient air.^{1,2,3} The color variation on the sample surface could be due to the presence of different oxides of vanadium⁴ as a result of surface oxidation, after prolonged exposure of samples in the ambient air for various characterizations. A thickness variation of 8 to 12% is noticed at the sample edges that happens when the substrate is placed at an oblique angle for the deposition. The color changes particularly at the edges could also be due to the thickness variation in the sample edges.

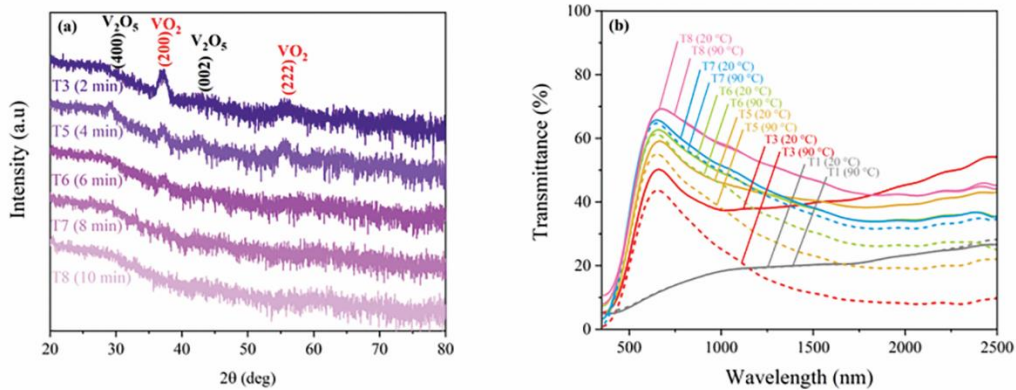


Fig. S4 (a) GIXRD patterns corresponding to the samples T3, T5, T6, T7, and T8 for 2θ ranging from 20 to 80 degrees. (b) Transmittance responses of the samples T1, T3, T5, T6, T7, and T8 under unpolarized light at the measurement temperatures 20 and 90 °C. The sample T1 corresponds to as-prepared STF vanadium, whereas T3, T5, T6, T7, and T8 are the samples subjected to different heat treatments. The oxidation annealing times of the samples T3, T5, T6, T7, and T8 are 2, 4, 6, 8, and 10 min respectively, with a constant annealing temperature of 450 °C in the ambient air.

Table S2. Comparison of the thermochromic performance of VO₂ thin films (grown by various techniques, different substrates, and thicknesses) with the present work

Sample	Substrate	Fabrication method	Thickness	Deposition configuration	T _{lum(avg)} (%)	ΔT _{ir(2000 nm)} (%)	ΔT _{sol} (%)
VO ₂ single layer	Quartz ⁵	PVD	130 nm	normal	39.7	45.1	10.2
	BK7 ⁶	DC sputtering	90 nm	normal	35.4		9.7
	BK7 ⁷	Reactive sputtering	50 nm	normal	37.3	44.4	6.1
	Soda-lime ⁸	HiPIMS	95 nm	normal	24.4		8.8
	HT glass ⁸	HiPIMS	95 nm	normal	22.0		10.6
	Quartz ⁸	HiPIMS	95 nm	normal	19.3		12.2
	Soda-lime ⁹	HiPIMS	88 nm	normal	30.5	37.0	4.0
	Fused Quartz ¹⁰	Sol-gel	65 nm	normal	68.2	30.0	4.6
	Float glass ¹¹	RF sputtering	120 nm	normal	24.8	25.6	4.6
	Fused silica ¹¹	RF sputtering	90 nm	normal	37.7	27.7	4.0
	Glass ¹²	Reactive sputtering	100 nm	normal	41.5		6.9
Glass ¹³	CVD	300 nm	normal	15.4		3.1	
STF VO ₂ (This work)	BK7	RF sputtering	130 nm	oblique angle (α = 85°)	41.2	37.3	8.9

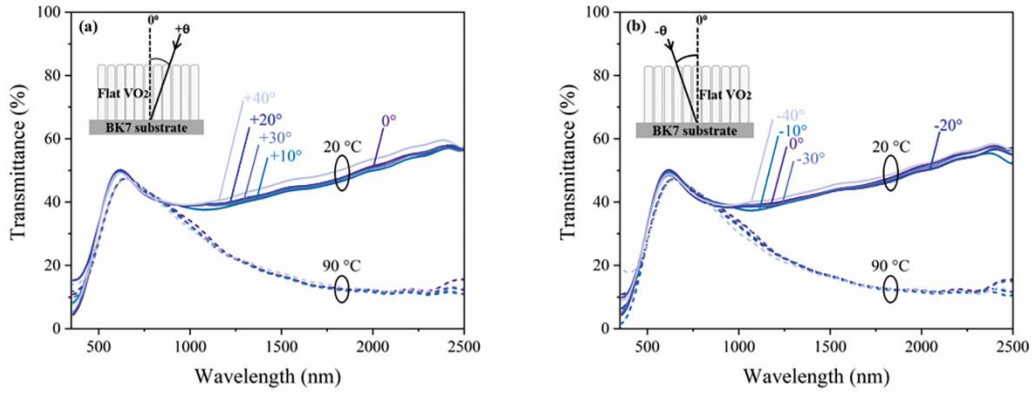


Fig. S5 Angular transmittance responses of flat VO₂ under unpolarized light at the measurement temperatures 20 and 90 °C (a) for the positive angles of incidence from +10° to +40° and (b) for the negative angles of incidence from -10° to -40° (in steps of 10°) with respect to 0°, where 0° is the measurement in the normal incidence. The insets in (a) and (b) are the schematics of the transmittance measurements for the positive and negative angles of incidence respectively in flat VO₂ with straight nanocolumns. The dotted lines in the inset indicate the substrate normal, and the arrow indicates the light ray.

Table S3. Comparison of thermochromic performance of recent work on STF VO₂ (transmittance measured in normal and oblique incidence) with the present work

Sample	Substrate	Fabrication method	Thickness	Deposition configuration	Tilt angle (β)	Light incidence angle	$T_{lum}(avg)$ (%)	ΔT_{nir} (%)	ΔT_{sol} (%)
STF VO ₂ (This work)	BK7	RF sputtering	130 nm	oblique angle ($\alpha = 85^\circ$)	20°	0°	41.2	7.0	8.9
						+30°	40.8	7.2	9.6
						-30°	39.3	6.5	8.4
STF VO ₂	BK7 ¹⁴	Thermal evaporation	≈500 nm	oblique angle ($\alpha = 85^\circ$)	47°	0°	33.8		6.4
						+30°	32.4		7.0
						-30°	34.4		6.1

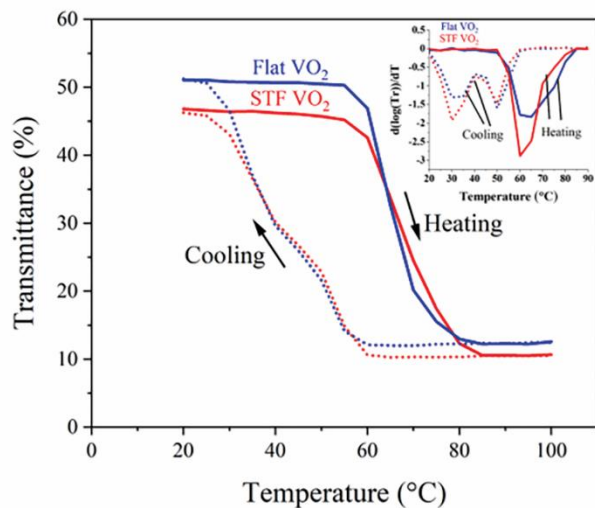


Fig. S6 Transmittance hysteresis loop of STF VO₂ and flat VO₂ at the wavelength of 2000 nm. The black arrows indicate heating and cooling directions. The inset shows the transmittance derivative curves of STF VO₂ and flat VO₂ versus the measurement temperature.

Table S4. Summary of thermal hysteresis characteristics of STF VO₂ and flat VO₂

Sample	T_c in heating and cooling branches (°C)		T_c (°C)	ΔT_c (°C)
	T_c(heating)	T_c(cooling)		
STF VO ₂	65	30/50	47.5/57.5	35/15
Flat VO ₂	60	30/50	45/55	30/10

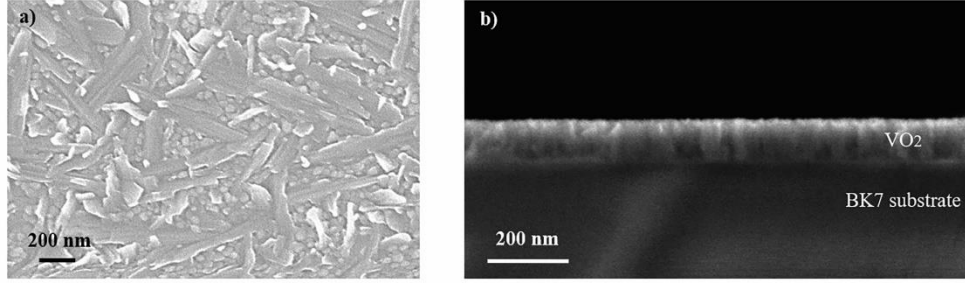


Fig. S7 SEM (a) top-view and (b) cross-section images of flat VO₂ annealed at 450 °C for 2 min.

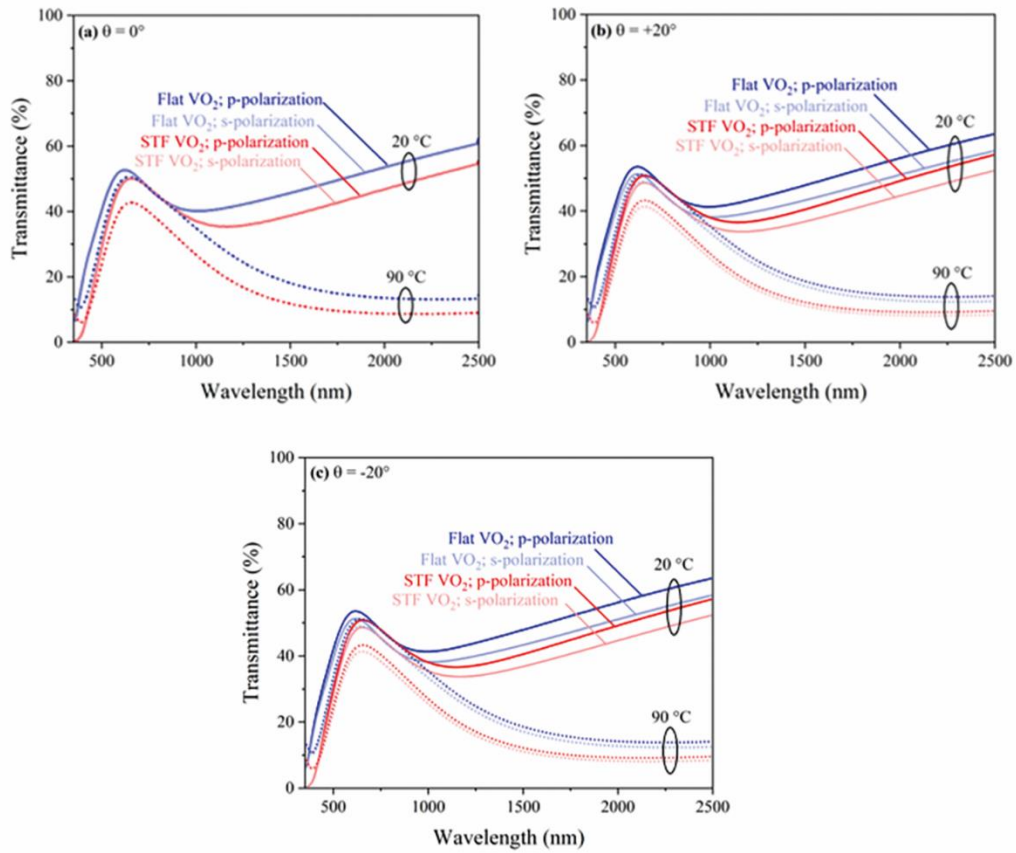


Fig. S8 Polarization (*s* and *p*-polarizations) dependence of the transmittance spectra at both 20 and 90 °C for the flat and STF VO₂ samples at (a) $\theta = 0^\circ$ (b) $\theta = +20^\circ$ (c) $\theta = -20^\circ$. The thickness of both flat and STF VO₂ is 130 nm, while f_a of STF VO₂ is 89%.

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